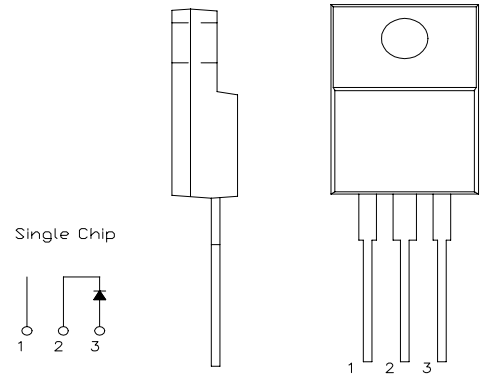


FRD Type : FSF10A20B

OUTLINE DRAWING

FEATURES

- * Fully Molded Isolation Case
- * Ultra – Fast Recovery
- * Low Forward Voltage Drop
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * 200 Volts thru 600 Volts Types Available



Maximum Ratings

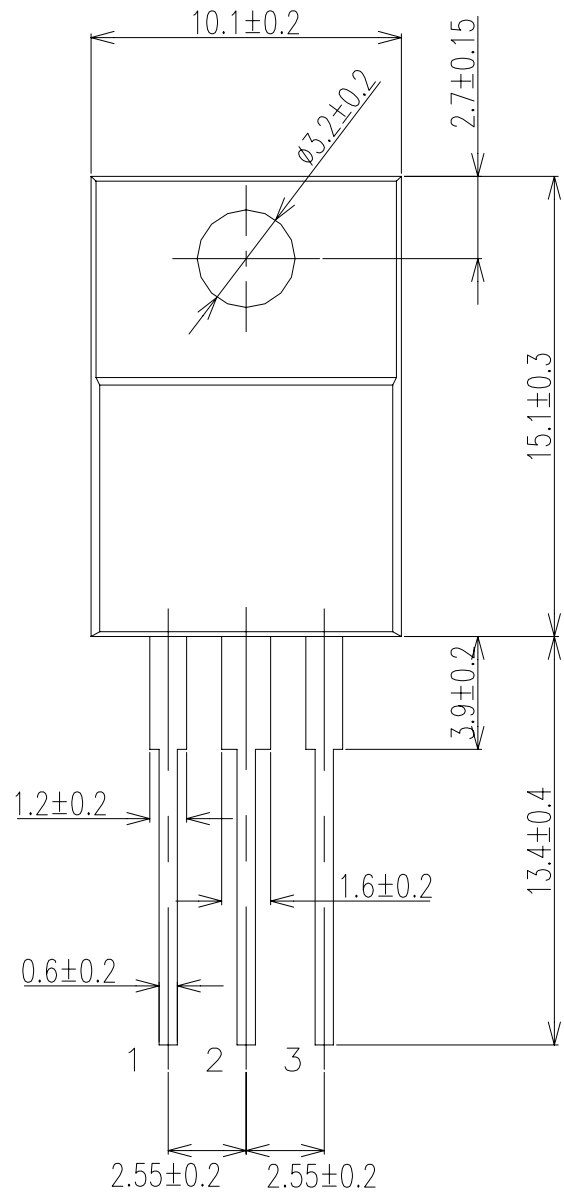
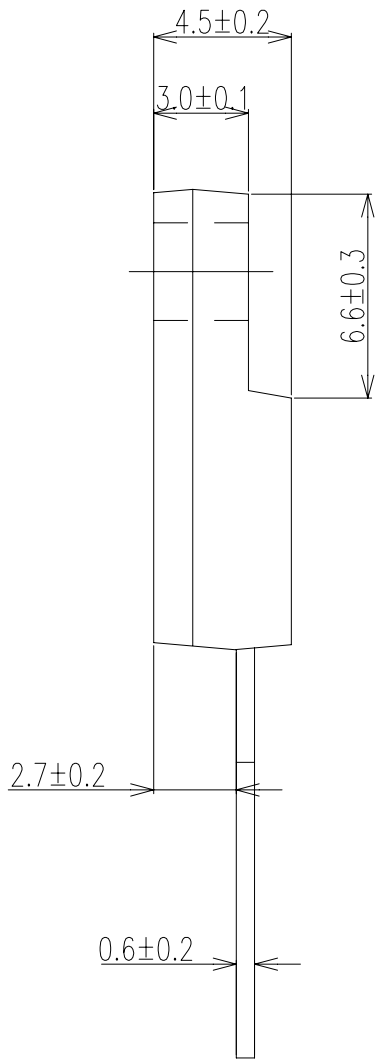
Approx Net Weight:1.75g

Rating	Symbol	FSF10A20B		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	200		V
Non-repetitive Peak Reverse Voltage	V_{RSM}	220		
Average Rectified Output Current	I_O	10	$T_c=100^\circ\text{C}$ 50 Hz Half Sine Wave Resistive Load	A
RMS Forward Current	$I_{F(RMS)}$	15.7		A
Surge Forward Current	I_{FSM}	120	50 Hz Half Sine Wave, 1cycle Non-repetitive	A
Operating Junction Temperature Range	T_{jw}	- 40 to + 150		$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150		$^\circ\text{C}$
Mounting torque		0.5	Recommended value	N.m

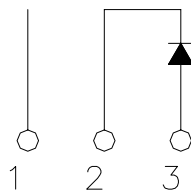
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j= 25^\circ\text{C}, V_{RM}= V_{RRM}$	-	-	25	μA
Peak Forward Voltage	V_{FM}	$T_j= 25^\circ\text{C}, I_{FM}= 10\text{A}$	-	-	1.03	V
Reverse Recovery Time	t_{rr}	$I_{FM}= 10\text{A},$ $-di/dt= 50 \text{ A}/\mu\text{s}, T_a= 25^\circ\text{C}$	-	-	35	ns
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	4	$^\circ\text{C}/\text{W}$
	$R_{th(c-f)}$	Case to Fin	-	-	1.5	

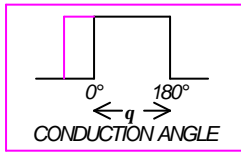
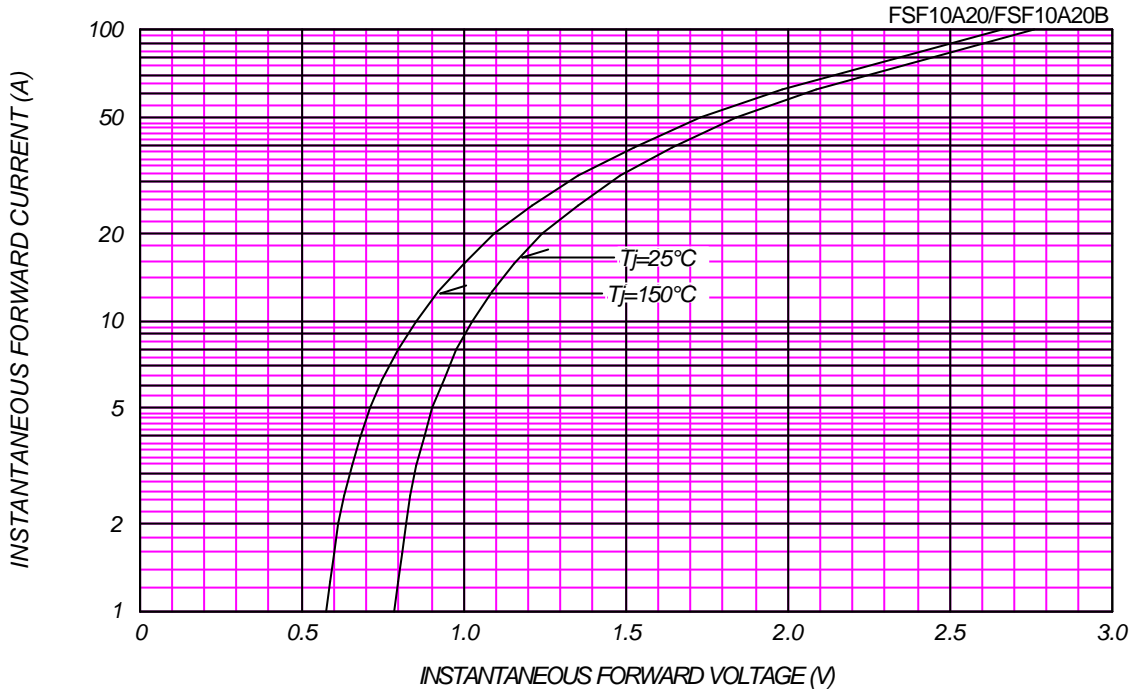
FSF_A_B OUTLINE DRAWING (Dimensions in mm)



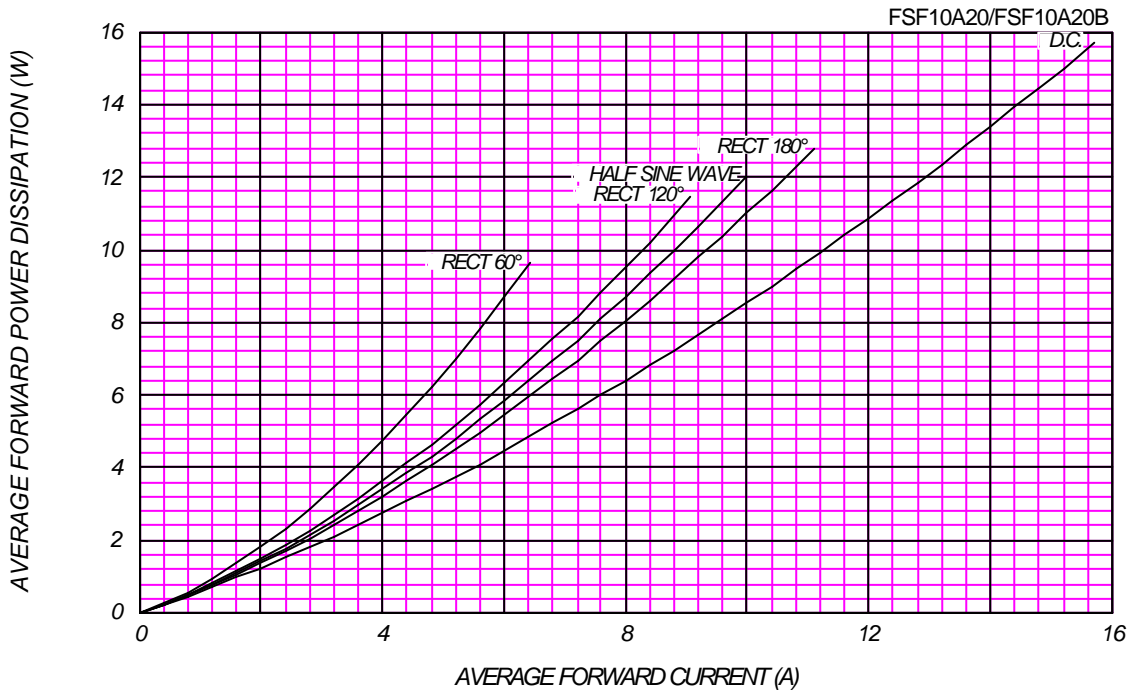
Single Chip

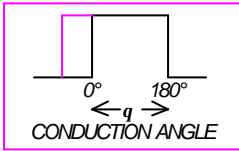


FORWARD CURRENT VS. VOLTAGE

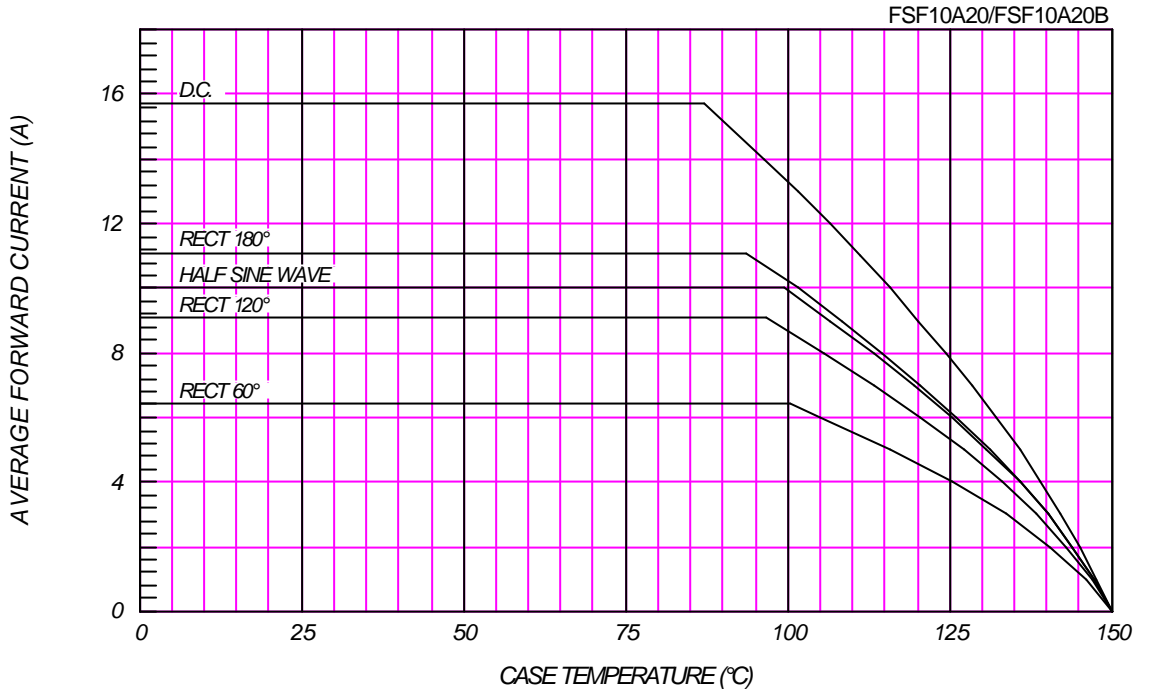


AVERAGE FORWARD POWER DISSIPATION





AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE



SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

